

VCTB5V0P216YW

Bi-directional Low Capacitance ESD Protector

Description

The VCTB5V0P216YW protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.

Feature

- 100W peak pulse power per line ($t_P = 8/20\mu s$)
- DFN1006-2L package
- Replacement for MLV(0402)
- Bidirectional configurations
- Response time is typically $< 1ns$
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to
IEC61000-4-2(ESD) $\pm 15KV(air)$, $\pm 12KV(contact)$;
IEC61000-4-4 (EFT) 40A (5/50ns)

Applications

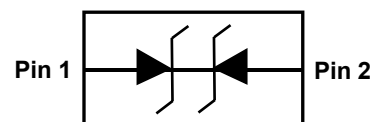
- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Mechanical Characteristics

- Mounting position: Any
- Qualified max reflow temperature: $260^{\circ}C$
- Device meets MSL 1 requirements
- DFN1006-2L without plating



DFN1006-2L(Bottom View)



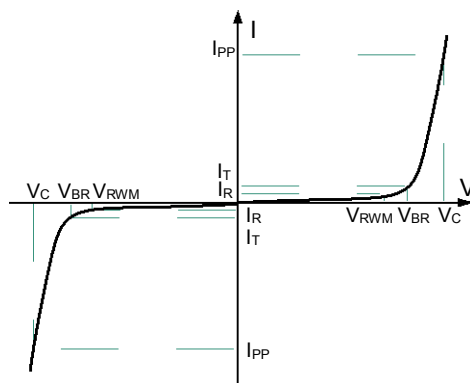
Circuit Diagram

DEVICE MARKING CODES:

Device Type	Marking	Shipping
VCTB5V0P216YW	B1 、 L5	10,000/Tape & Reel

Electronics Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
P_{PP}	Peak Pulse Power
C_J	Junction Capacitance
I_F	Forward Current
V_F	Forward Voltage @ I_F



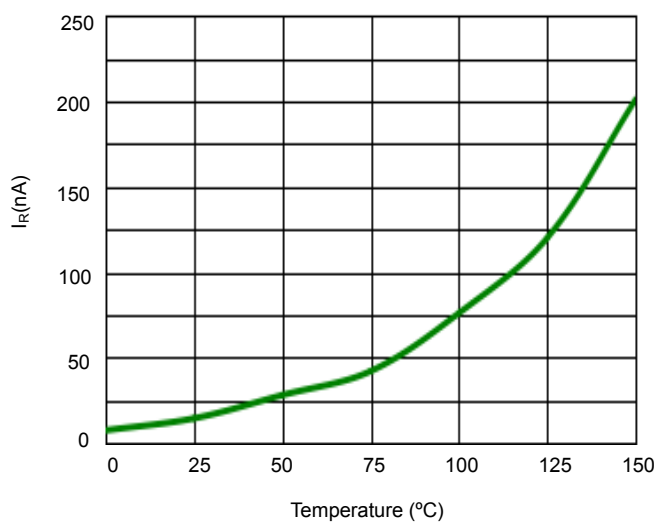
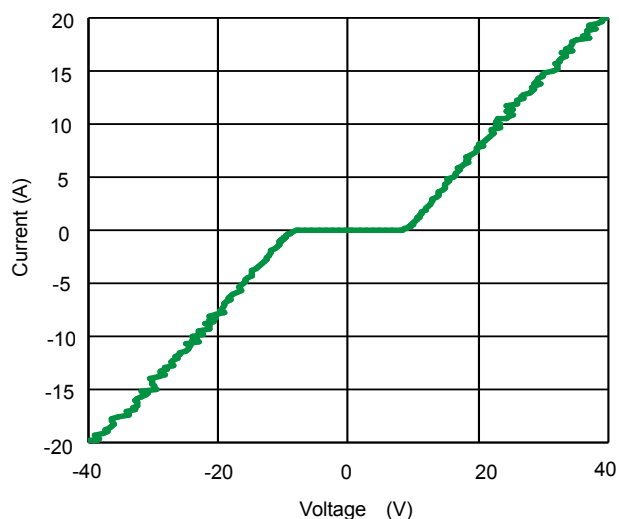
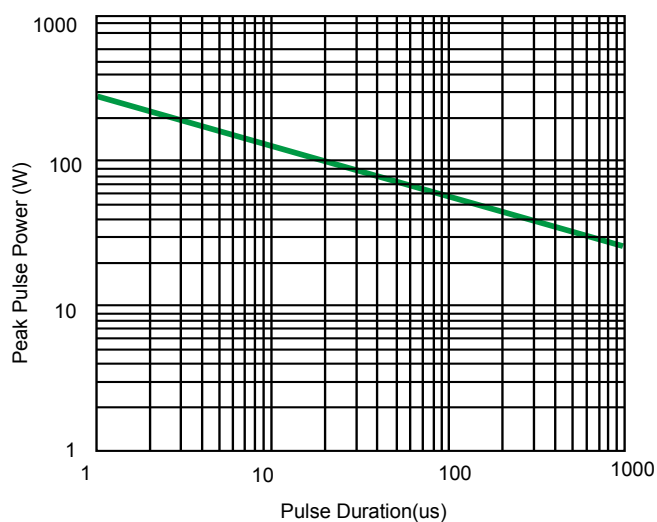
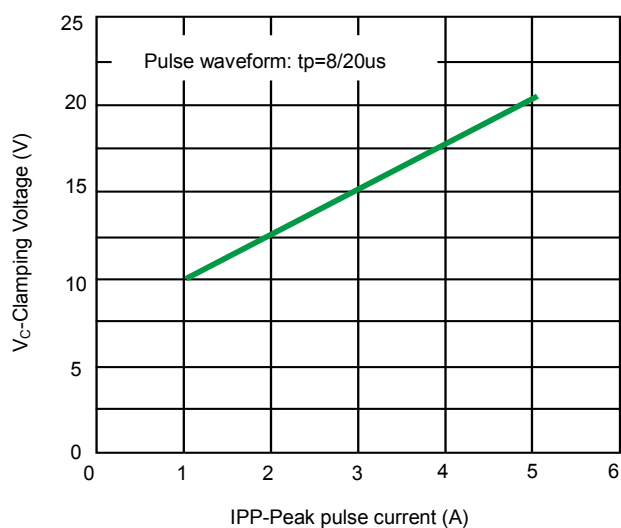
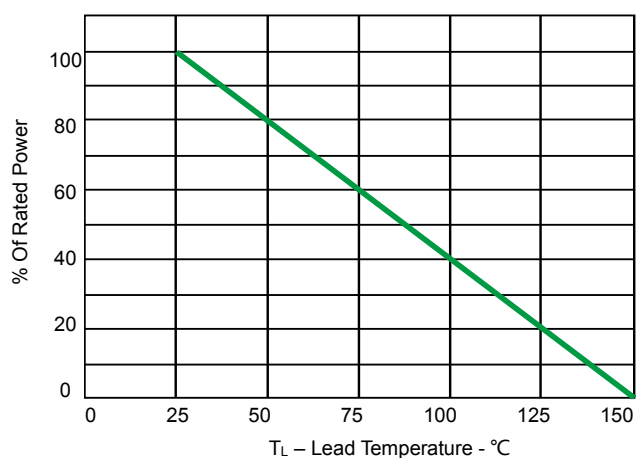
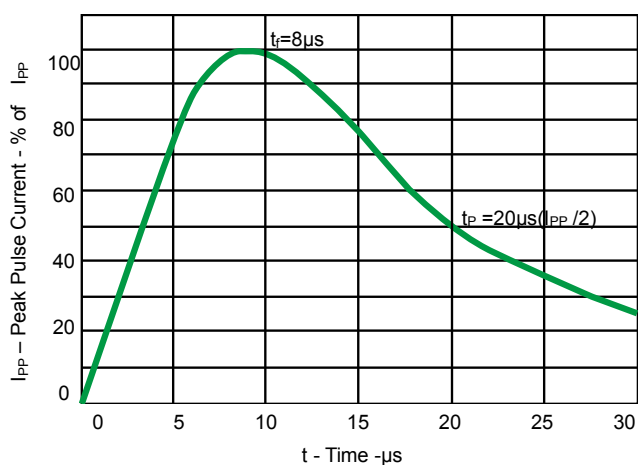
Electrical characteristics per line@25°C (unless otherwise specified)

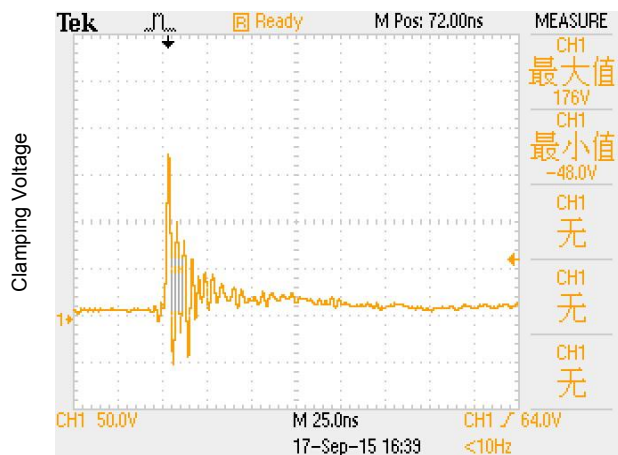
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Peak Reverse Working Voltage	V_{RWM}				5	V
Breakdown Voltage	V_{BR}	$I_t = 1mA$	5.6		8.5	V
Reverse Leakage Current	I_R	$V_{RWM} = 5V$ $T=25^{\circ}C$			1.0	μA
Maximum Reverse Peak Pulse Current	I_{PP}			5.5		A
Clamping Voltage	V_C	$I_{PP}=1A$			10	V
Clamping Voltage	V_C	$I_{PP}=3A$			15	V
Clamping Voltage	V_C	$I_{PP}=5A$			21	V
Junction Capacitance	C_j	$V_R=0V$ $f = 1MHz$		0.25	0.35	pF

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p=8/20\mu s$)	P_{pp}	100	W
Peak Pulse Current ($t_p=8/20\mu s$)	I_{pp}	5	A
Operating Temperature	T_J	-55 to 150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}C$

Typical Characteristics



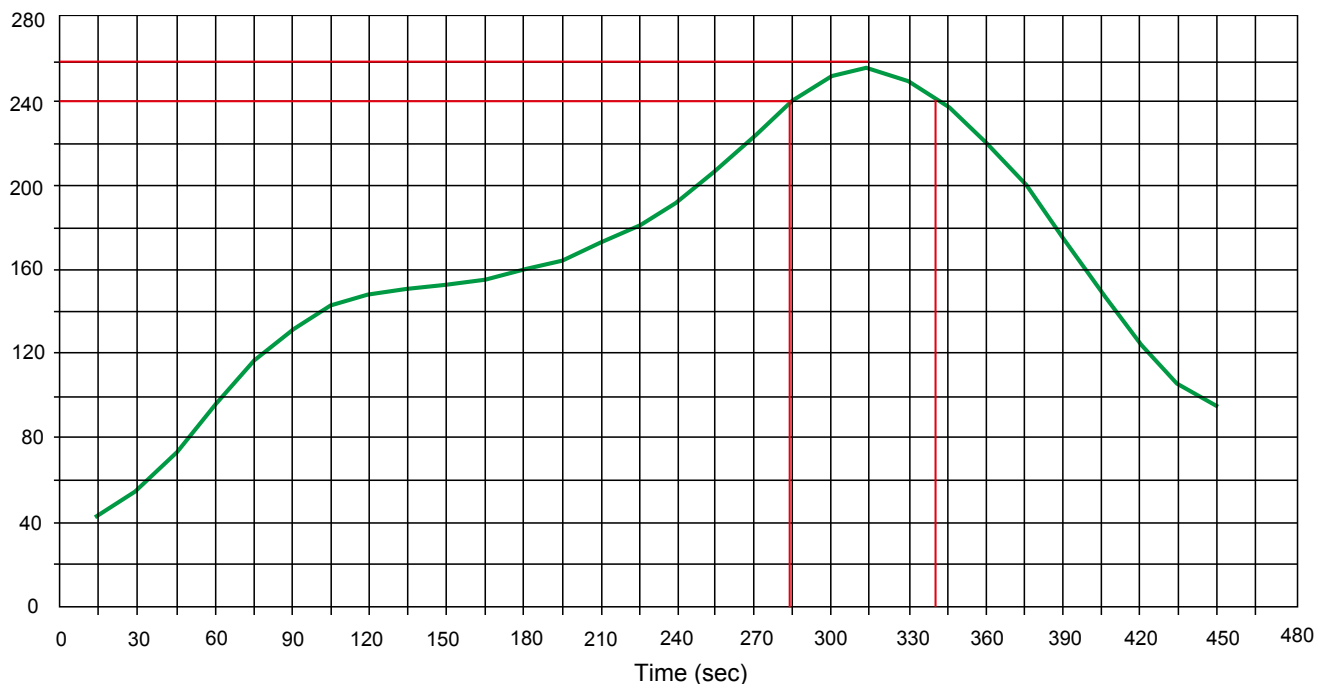


ESD clamping

Fig 7 (8kV contact discharge per IEC61000-4-2)

Solder Reflow Recommendation

Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec

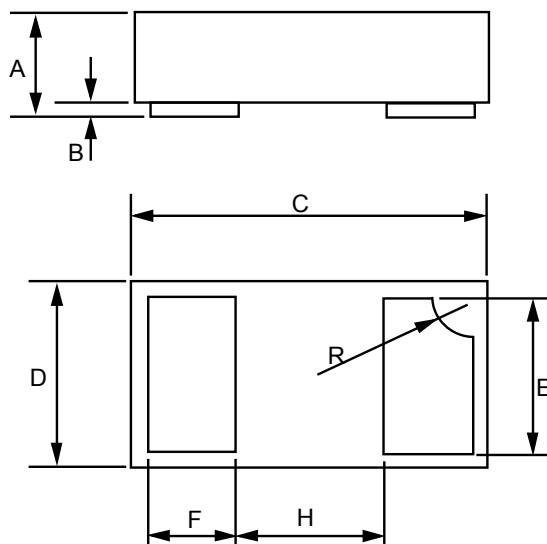


PCB Design

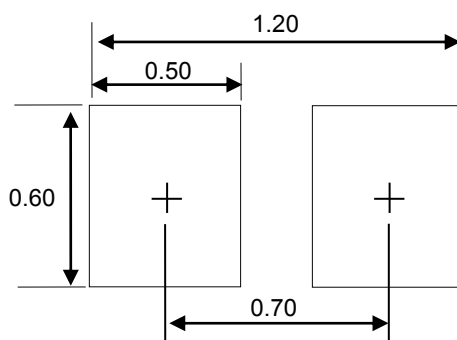
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

Product dimension (DFN1006-2L)



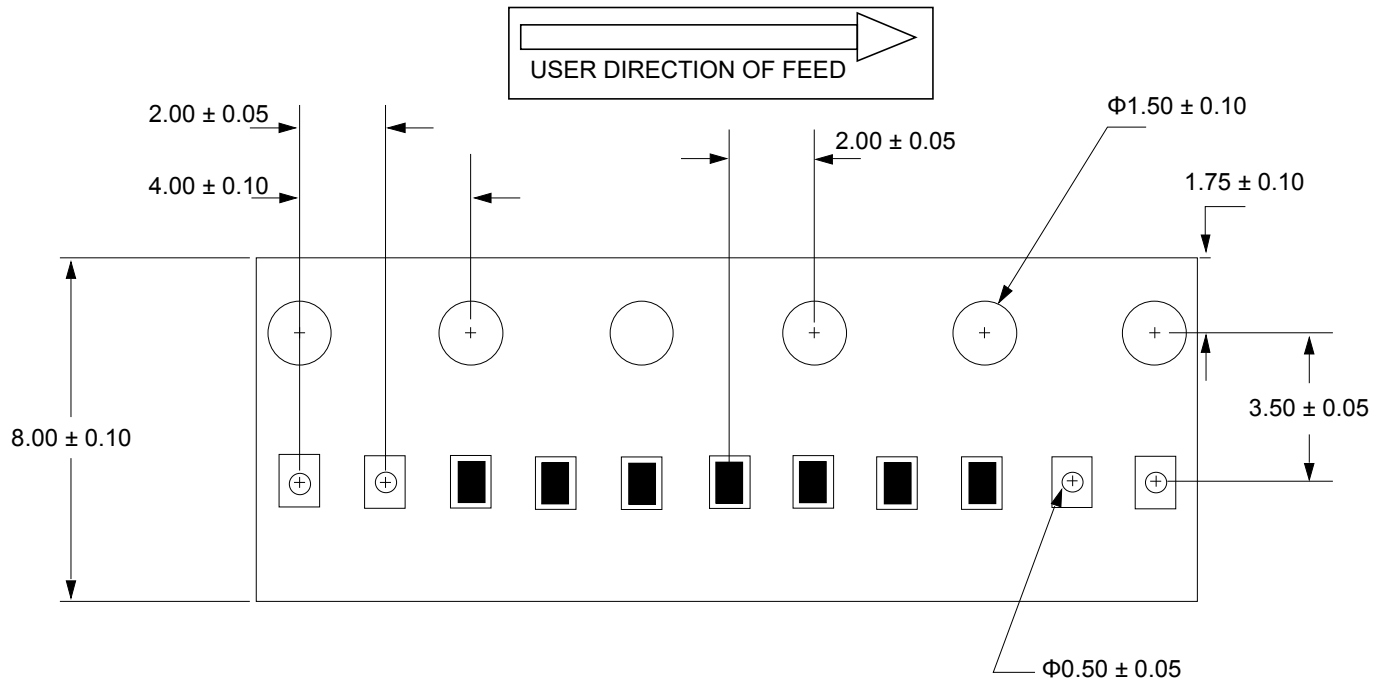
Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.013	0.020	0.34	0.50
B	0.000	0.002	0.00	0.05
C	0.037	0.043	0.95	1.080
D	0.022	0.027	0.55	0.680
E	0.016	0.024	0.40	0.60
F	0.008	0.012	0.20	0.30
H	0.015Typ.		0.40Typ.	
R	0.001	0.005	0.05	0.15



Unit:mm

Suggested PCB Layout

Load with information



Unit: mm

Important Notice and Disclaimer

Weforsemi reserves the right to make changes to this document and its products and specifications at any time without notice. Customers should obtain and confirm the latest product information and specifications before final design, purchase or use.

Weforsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Weforsemi assume any liability for application assistance or customer product design. Weforsemi does not warrant or accept any liability with products which are purchased or used for any unintended or unauthorized application.

No license is granted by implication or otherwise under any intellectual property rights of Weforsemi .

Weforsemi products are not authorized for use as critical components in life support devices or systems without express written approval of Weforsemi .